

Patent Abstracts of Japan

PUBLICATION NUMBER : 60198832
PUBLICATION DATE : 08-10-85

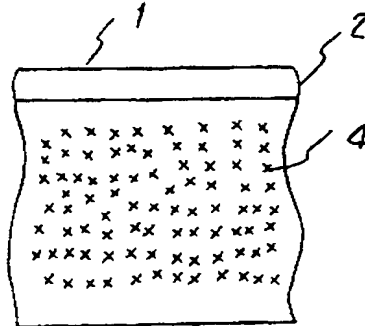
APPLICATION DATE : 23-03-84
APPLICATION NUMBER : 59055607

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INT.CL. : H01L 21/322

TITLE : SEMICONDUCTOR DEVICE



ABSTRACT : PURPOSE: To obtain a substrate for IC having high reliability by a method wherein an Si wafer having an intrinsic gettering effect, and moreover made concentration of O_2 within depth of $10\mu m$ from the surface of the Si substrate to $5 \times 10^{17}/cm^3$ or less, and the surface region thereof is made to no defect layer substantially is used.

CONSTITUTION: Heat treatments of a high temperature and a low temperature are performed to an Si wafer having concentration of O_2 of $12 \sim 18 \times 10^{17}/cm^3$ normally, and concentration of O_2 of the layer within depth of $10\mu m$ from the surface 1, which is the active region of a transistor, is made to $5 \times 10^{17}/cm^3$ or less. An actually no defect layer is formed in such a way, the defect of the element activating region 2 thereof is reduced to $10^3 \sim 10^6/cm^3$, and an intrinsic gettering effect is generated. Moreover lattice defects 4 of a large number are left as they are like the beginning in a region under the region 2. When a substrate obtained in such a way is used, a transistor having no characteristic inferiority and no characteristic variation can be obtained.

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